

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

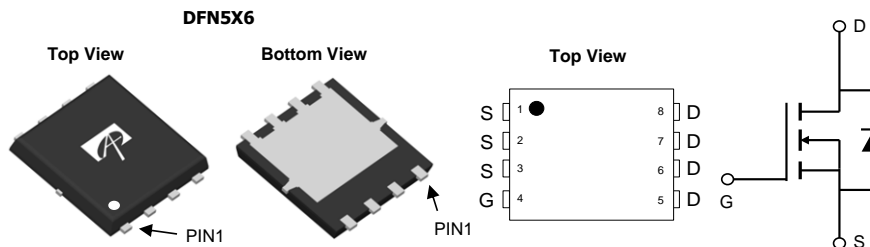
Applications

- High performance ORing, Efuse
- Ultra high current battery charge/discharge

Product Summary

V_{DS}	25V
I_D (at $V_{GS}=10V$)	400A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 0.73m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 1.08m Ω

100% UIS Tested
 100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONS32100	DFN 5x6	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}^G$	400
		$T_C=100^\circ\text{C}$	370
Pulsed Drain Current C ($\leq 10\mu\text{s}$)	I_{DM}	1500	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	73
		$T_A=70^\circ\text{C}$	60
Avalanche Current C	I_{AS}	80	A
Avalanche energy $L=0.1\text{mH}^C$	E_{AS}	320	mJ
Power Dissipation B	P_D	$T_C=25^\circ\text{C}$	400
		$T_C=100^\circ\text{C}$	160
Power Dissipation A	P_{DSM}	$T_A=25^\circ\text{C}$	6.2
		$T_A=70^\circ\text{C}$	4
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	$R_{\theta JA}$	15	20	$^\circ\text{C/W}$
Maximum Junction-to-Ambient $^A D$		Steady-State	40	50
Maximum Junction-to-Case	$R_{\theta JC}$	0.26	0.31	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.6	1.1	1.6	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		0.6 0.9	0.73 1.1	mΩ
		V _{GS} =4.5V, I _D =20A		0.85	1.08	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		85		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.6	1	V
I _S	Maximum Body-Diode Continuous Current				200	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz		15200		pF
C _{oss}	Output Capacitance			2000		pF
C _{rss}	Reverse Transfer Capacitance			1400		pF
R _g	Gate resistance	f=1MHz	0.7	1.4	2.1	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A		240		nC
Q _g (4.5V)	Total Gate Charge			115		nC
Q _{gs}	Gate Source Charge			27		nC
Q _{gd}	Gate Drain Charge			35		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =12.5V, R _L =0.625Ω, R _{GEN} =3Ω		15		ns
t _r	Turn-On Rise Time			20		ns
t _{D(off)}	Turn-Off DelayTime			160		ns
t _f	Turn-Off Fall Time			50		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		25		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		70		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

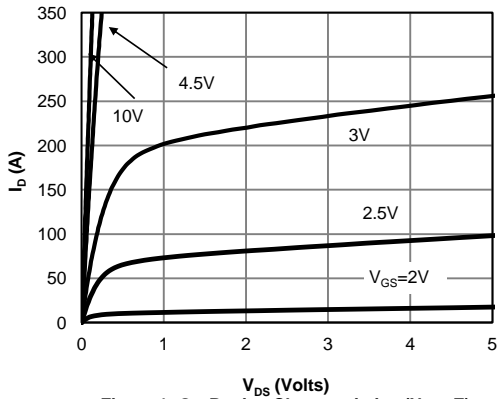


Figure 1: On-Region Characteristics (Note E)

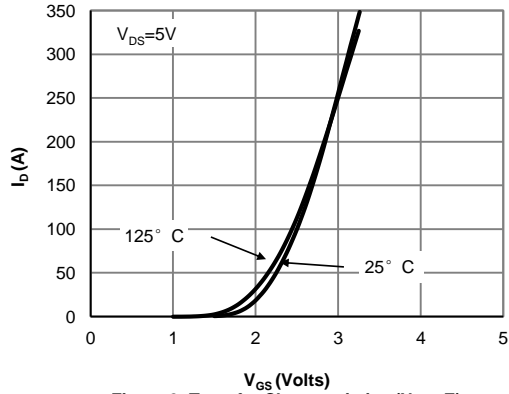


Figure 2: Transfer Characteristics (Note E)

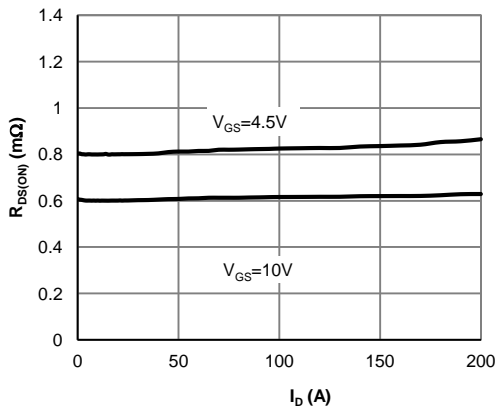


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

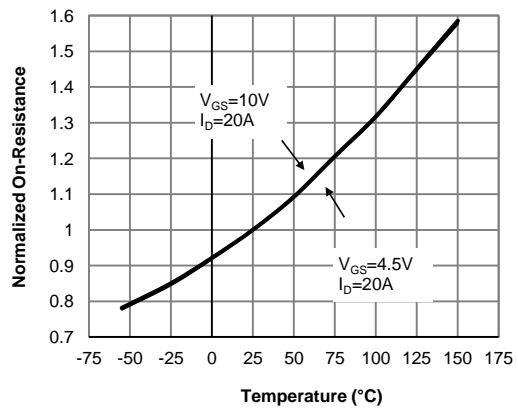


Figure 4: On-Resistance vs. Junction Temperature (Note E)

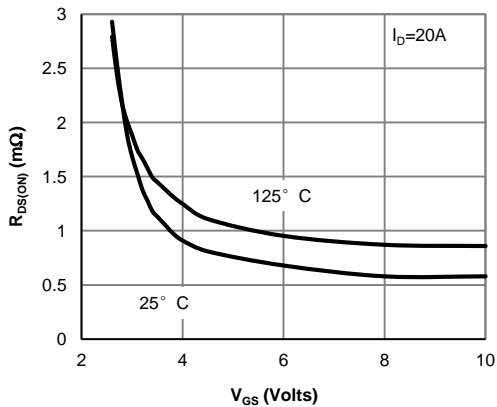


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

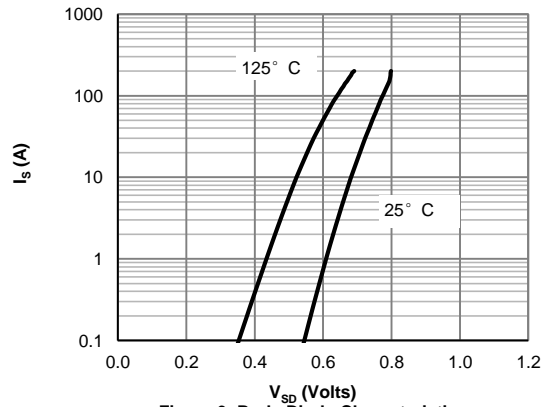


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

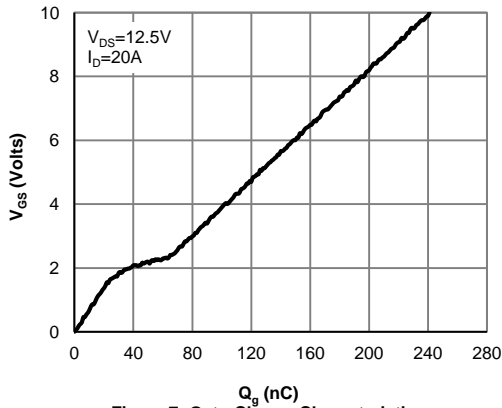


Figure 7: Gate-Charge Characteristics

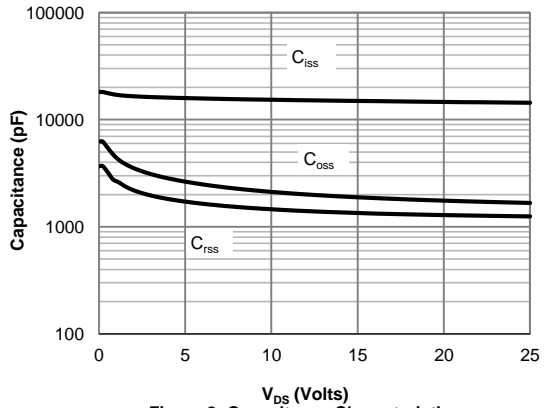


Figure 8: Capacitance Characteristics

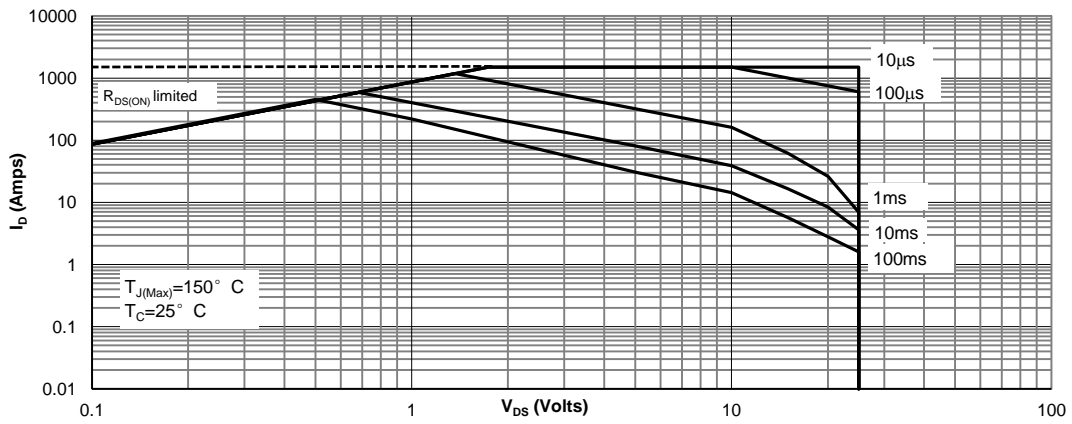


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

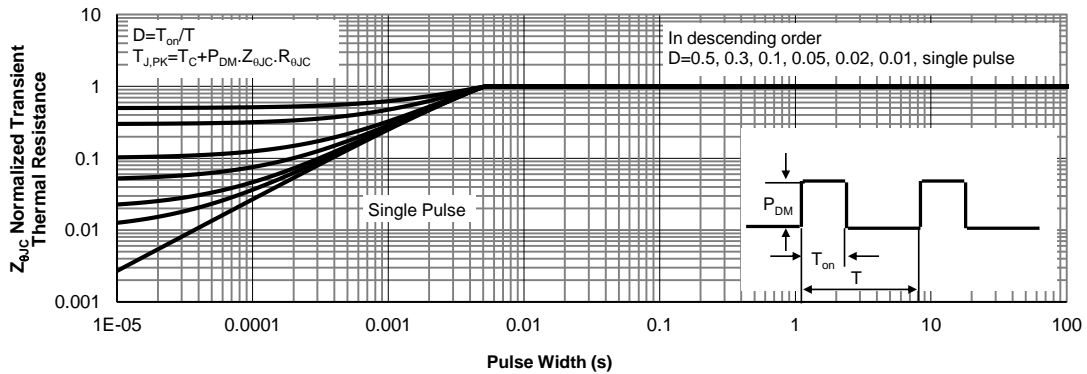


Figure 10: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

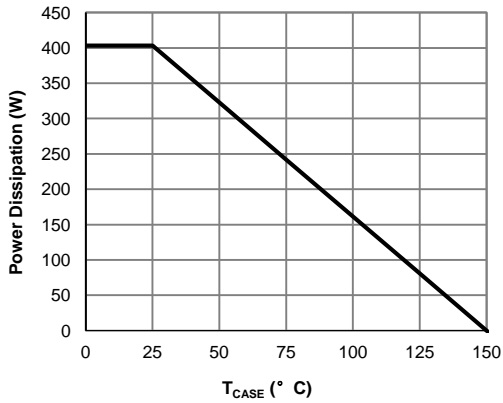


Figure 11: Power De-rating (Note F)

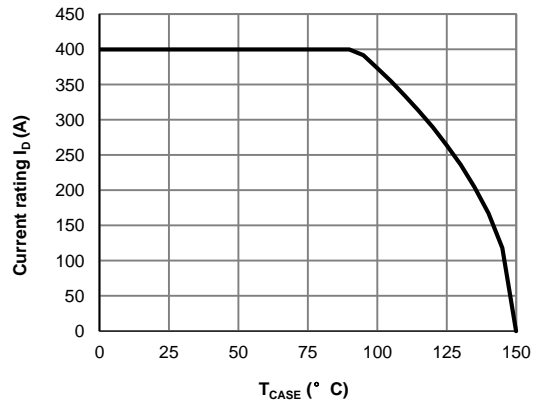


Figure 12: Current De-rating (Note F)

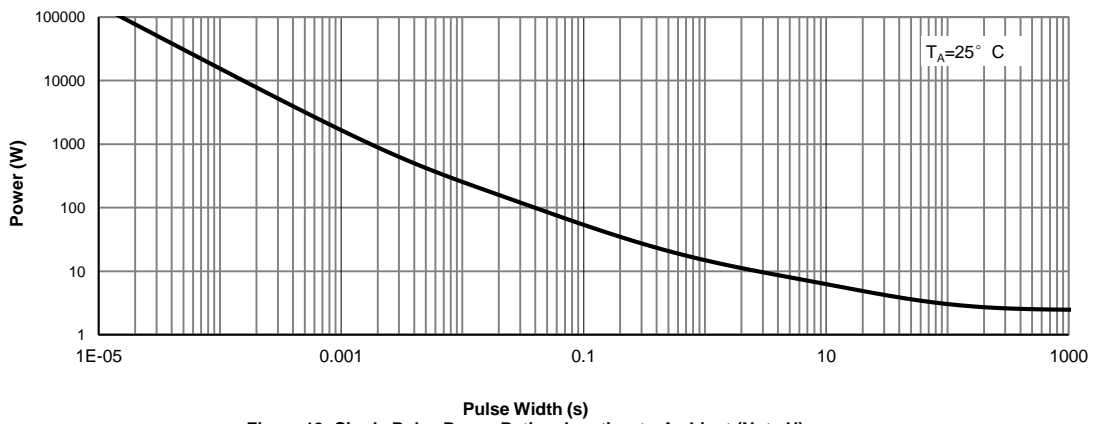


Figure 13: Single Pulse Power Rating Junction-to-Ambient (Note H)

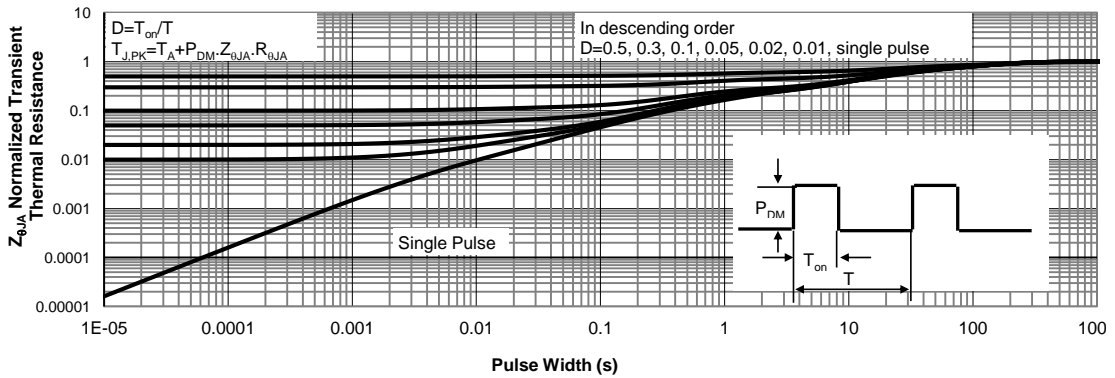


Figure 14: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

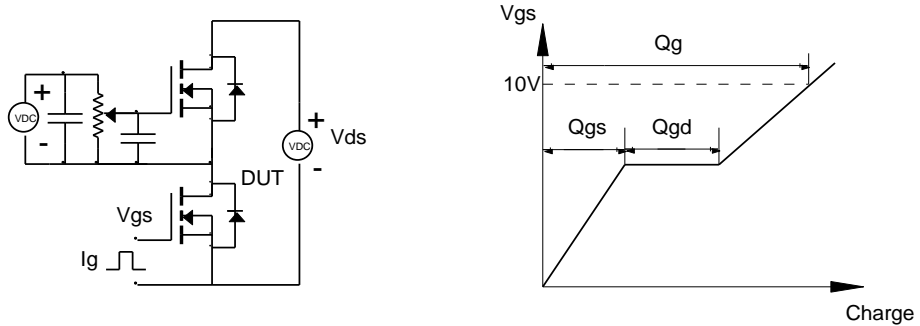


Figure B: Resistive Switching Test Circuit & Waveforms

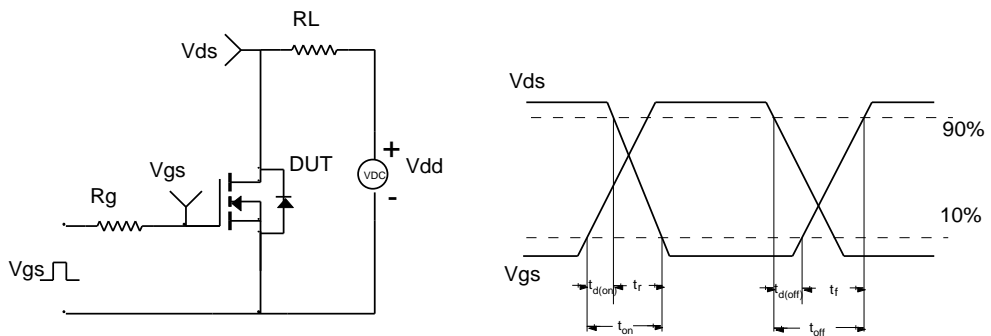


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

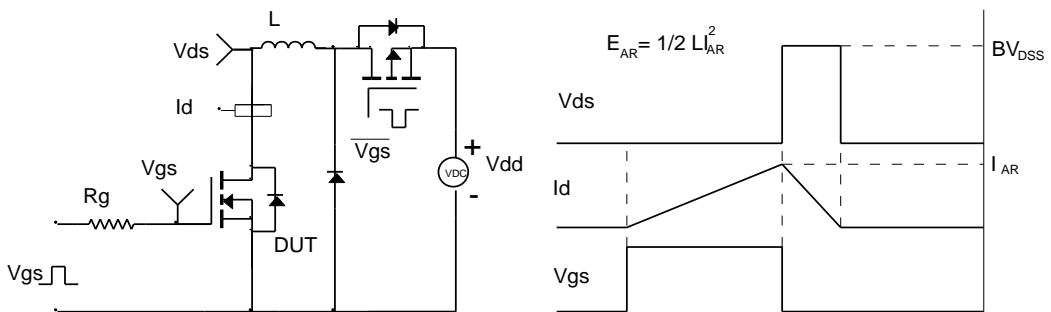
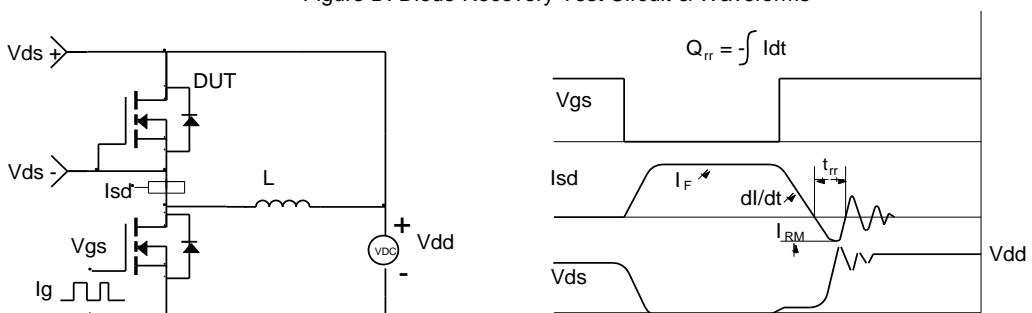


Figure D: Diode Recovery Test Circuit & Waveforms



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